## 1. General description

Planar passivated Silicon Controlled Rectifier with ultra-sensitive gate in a SOT54 (TO-92) plastic package.

#### 2. Features and benefits

- High voltage capability
- · Planar passivated for voltage ruggedness and reliability
- Ultra sensitive gate

## 3. Applications

- Electronic ballasts
- Safety shut down and protection circuits
- Sensing circuits
- · Smoke detectors
- Switched Mode Power Supplies

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{RRM}$	repetitive peak reverse voltage		-	-	600	V
I <sub>T(AV)</sub>	average on-state current	half sine wave; T <sub>lead</sub> ≤ 67 °C; <u>Fig. 1</u>	-	-	0.51	Α
I <sub>T(RMS)</sub>	RMS on-state current	half sine wave; $T_{lead} \le 67 \text{ °C}$ ; Fig. 2; Fig. 3	-	-	0.8	Α
I <sub>TSM</sub>	non-repetitive peak on- state current	half sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 10 \text{ ms}$ ; Fig. 4; Fig. 5	-	-	8	Α
		half sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 8.3 ms	-	-	9	Α
Tj	junction temperature		-	-	125	°C
Static chara	acteristics					
I <sub>GT</sub>	gate trigger current	$V_D$ = 12 V; $I_T$ = 10 mA; $T_j$ = 25 °C; Fig. 7	0.5	-	7	μΑ
Dynamic ch	naracteristics					
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 402 V; $T_j$ = 125 °C; $R_{GK}$ = 1 kΩ; $(V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; Fig. 13; Fig. 14	75	-	-	V/µs

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# **5. Pinning information**

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Α	anode		А <del>- [-] -</del> К
2	G	gate		Ġ sym037
3	K	cathode	TO-92 (SOT54)	Symos

# 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package					
	Name	Description	Version			
N0118GA	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54			

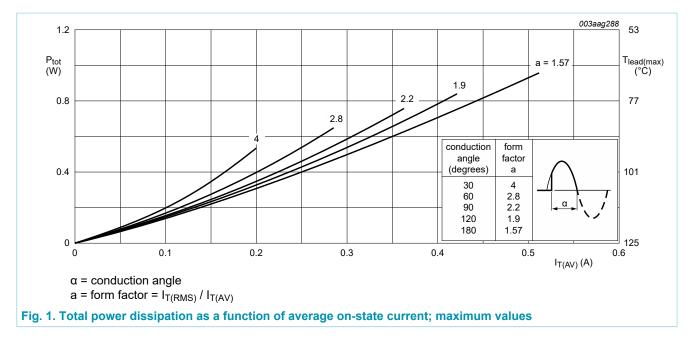
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# 7. Limiting values

**Table 4. Limiting values** 

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	600	V
$V_{RRM}$	repetitive peak reverse voltage		-	600	V
I <sub>T(AV)</sub>	average on-state current	half sine wave; T <sub>lead</sub> ≤ 67 °C; <u>Fig. 1</u>	-	0.51	Α
I <sub>T(RMS)</sub>	RMS on-state current	half sine wave; T <sub>lead</sub> ≤ 67 °C; <u>Fig. 2</u> ; <u>Fig. 3</u>	-	0.8	Α
I <sub>TSM</sub>	non-repetitive peak on- state current	half sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 10 ms; Fig. 4; Fig. 5	-	8	Α
		half sine wave; T <sub>j(init)</sub> = 25 °C; t <sub>p</sub> = 8.3 ms	-	9	Α
I <sup>2</sup> t	I <sup>2</sup> t for fusing	t <sub>p</sub> = 10 ms; SIN	-	0.32	A²s
dl <sub>T</sub> /dt	rate of rise of on-state current	$I_T = 0.8 \text{ A}$ ; $I_G = 10 \text{ mA}$ ; $dI_G/dt = 0.1 \text{ A/}\mu\text{s}$	-	50	A/µs
I <sub>GM</sub>	peak gate current		-	1	Α
$V_{RGM}$	peak reverse gate voltage		-	5	V
$P_{GM}$	peak gate power		-	2	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.1	W
T <sub>stg</sub>	storage temperature		-40	150	°C
T <sub>j</sub>	junction temperature		-	125	°C



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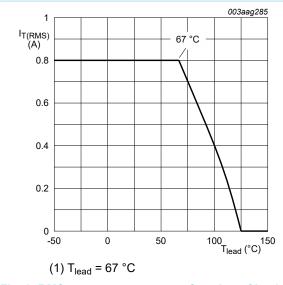
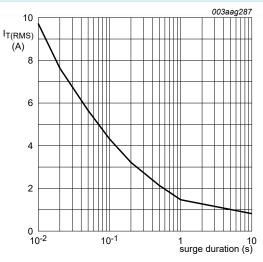


Fig. 2. RMS on-state current as a function of lead temperature; maximum values



f = 50 Hz;  $T_{lead}$  = 67 °C

Fig. 3. RMS on-state current as a function of surge duration; maximum values

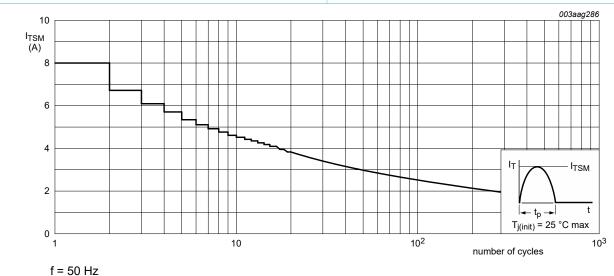
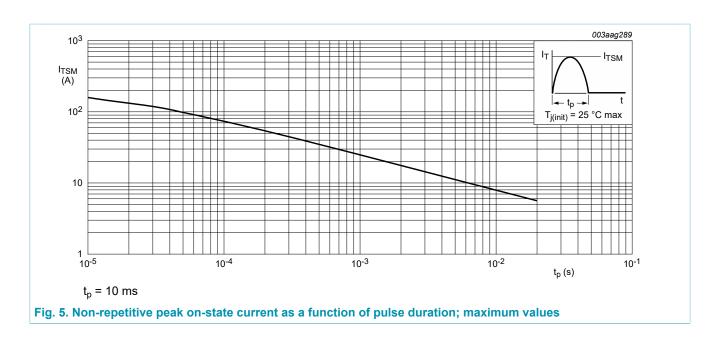


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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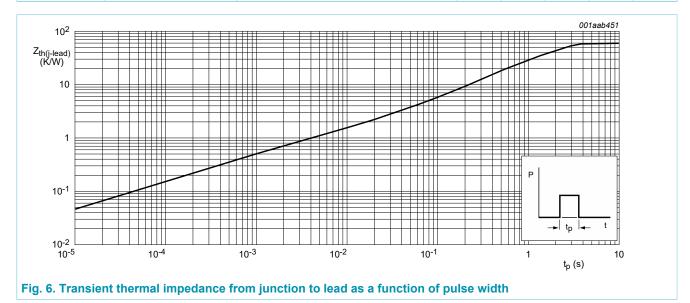


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#### 8. Thermal characteristics

**Table 5. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-lead)</sub>	thermal resistance from junction to lead	<u>Fig. 6</u>	-	-	60	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	printed circuit board mounted: lead length = 4 mm	-	150	-	K/W



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### 9. Characteristics

**Table 6. Characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V}; I_T = 10 \text{ mA}; T_j = 25 \text{ °C};$ Fig. 7	0.5	-	7	μΑ
IL	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T_j = 25 ^{\circ}\text{C}; Fig. 8$	-	-	6	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u> ; <u>Fig. 10</u>	-	-	5	mA
$V_{T}$	on-state voltage	I <sub>T</sub> = 1.6 A; T <sub>j</sub> = 25 °C; <u>Fig. 11</u>	-	1.4	1.95	V
$V_{GT}$	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 12	-	-	0.8	V
I <sub>D</sub>	off-state current	V <sub>D</sub> = 400 V; T <sub>j</sub> = 25 °C	-	-	10	μA
		$V_D = 600 \text{ V}; R_{GK(ext)} = 1 \text{ k}\Omega; T_j = 125 °C$	-	-	100	μA
I <sub>R</sub>	reverse current	$V_R = 600 \text{ V}; T_j = 25 \text{ °C}; R_{GK(ext)} = 1 \text{ k}\Omega$	-	-	10	μA
		$V_R = 600 \text{ V}; T_j = 125 \text{ °C}; R_{GK(ext)} = 1 \text{ k}\Omega$	-	-	100	μA
Dynamic ch	naracteristics					,
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 402 V; $T_j$ = 125 °C; $R_{GK}$ = 1 kΩ; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; Fig. 13; Fig. 14	75	-	-	V/µs

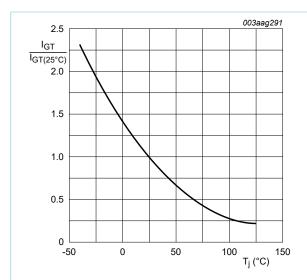


Fig. 7. Normalized gate trigger current as a function of junction temperature

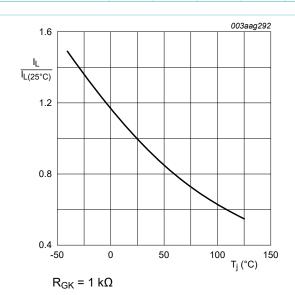


Fig. 8. Normalized latching current as a function of junction temperature

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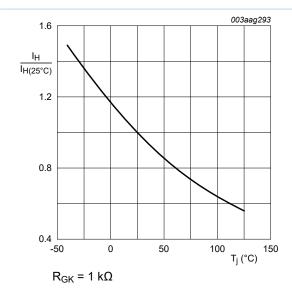


Fig. 9. Normalized holding current as a function of junction temperature

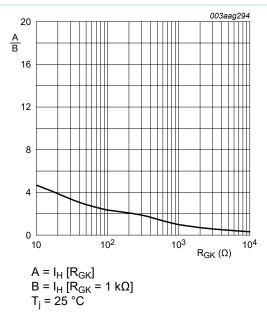
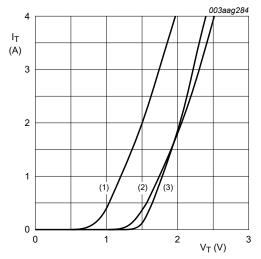


Fig. 10. Normalized holding current as a function of gate-cathode resistance (typical values)



 $V_o = 1.383 \text{ V}; R_s = 0.4 \Omega$ 

(1)  $T_j = 125$  °C; typical values (2)  $T_j = 125$  °C; maximum values (3)  $T_j = 25$  °C; maximum values

Fig. 11. On-state current as a function of on-state voltage

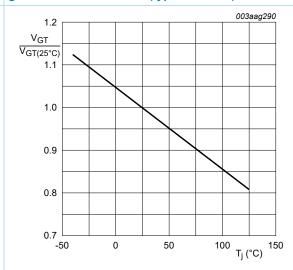


Fig. 12. Normalized gate trigger voltage as a function of junction temperature

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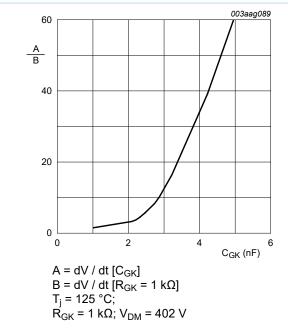


Fig. 13. Normalized dVd/dt immunity as a function of gate-cathode capacitance (typical values)

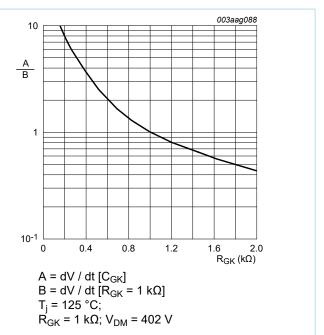


Fig. 14. Normalized dVd/dt immunity as a function of gate-cathode resistance (typical values)

# 10. Package outline

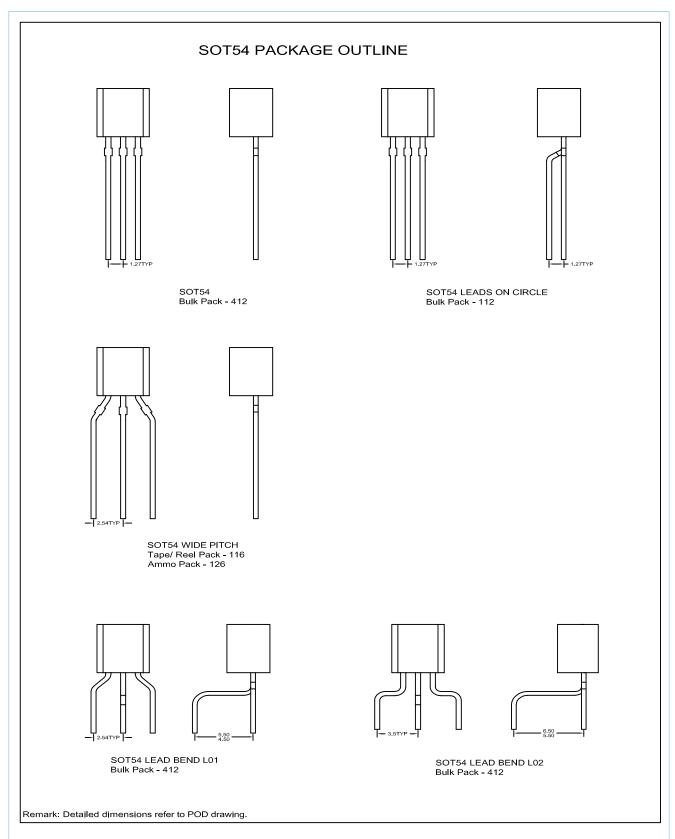


Fig. 15. Package outline TO-92 (SOT54)

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### 11. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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